

ENGR 305 Lab 8: Hand Calculations

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1 Part 1: PNP in Active Mode

1.1 Given Parameters

- **Voltage Supplies:** $V_+ = 15\text{ V}$, $V_- = -15\text{ V}$
- **Design Goals:** $I_C = 1\text{ mA}$, $V_B = 0\text{ V}$, $V_C = -5\text{ V}$
- **Transistor Model:** $\beta = 100$
- **Assumption:** Active region $V_{EB(\text{on})} = 0.7\text{ V}$

1.2 Circuit Analysis

The circuit is a standard four-resistor voltage divider bias for a PNP transistor.

- R_E is connected from V_+ to the Emitter.
- R_C is connected from the Collector to V_- .
- R_1 is connected from V_+ to the Base.
- R_2 is connected from the Base to V_- .

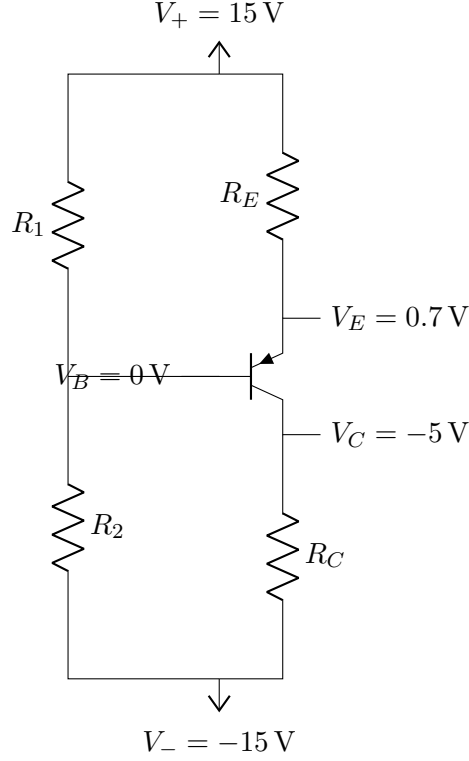


Figure 1: Part 1: PNP in Active Mode Circuit

1.3 Calculations

1. Calculate Base and Emitter Currents (I_B , I_E)

The base current is calculated from the collector current and β :

$$I_B = \frac{I_C}{\beta} = \frac{1 \text{ mA}}{100} = 0.01 \text{ mA} = 10 \mu\text{A}$$

The emitter current is the sum of the collector and base currents:

$$I_E = I_C + I_B = 1 \text{ mA} + 0.01 \text{ mA} = 1.01 \text{ mA}$$

2. Calculate Emitter Voltage (V_E)

The emitter voltage is found relative to the base voltage, using the $V_{EB(\text{on})}$ assumption:

$$V_E = V_B + V_{EB(\text{on})} = 0 \text{ V} + 0.7 \text{ V} = 0.7 \text{ V}$$

3. Calculate Emitter and Collector Resistors (R_E , R_C)

R_E is calculated using Ohm's law with the voltage drop across it ($V_+ - V_E$) and the current through it (I_E):

$$R_E = \frac{V_+ - V_E}{I_E} = \frac{15 \text{ V} - 0.7 \text{ V}}{1.01 \text{ mA}} = \frac{14.3 \text{ V}}{1.01 \text{ mA}} \approx 14.16 \text{ k}\Omega$$

R_C is calculated using the voltage drop across it ($V_C - V_-$) and the current through it (I_C):

$$R_C = \frac{V_C - V_-}{I_C} = \frac{-5 \text{ V} - (-15 \text{ V})}{1 \text{ mA}} = \frac{10 \text{ V}}{1 \text{ mA}} = 10 \text{ k}\Omega$$

4. Calculate Base Biasing Resistors (R_1 , R_2)

This problem is not fully specified, as there is one KCL equation at the base with two unknown resistors. We must make a design choice for the stiffness of the voltage divider. A common rule of thumb is to set the divider current (I_{divider}) to be at least 10 times the base current.

- $I_B = 10 \mu\text{A}$ (note: this current flows *out* of the PNP base).
- Let's set the current through R_2 as $I_{R2} = 10 \times I_B = 10 \times 10 \mu\text{A} = 100 \mu\text{A}$.

Now, we can find R_2 :

$$R_2 = \frac{V_B - V_-}{I_{R2}} = \frac{0 \text{ V} - (-15 \text{ V})}{100 \mu\text{A}} = \frac{15 \text{ V}}{0.1 \text{ mA}} = 150 \text{ k}\Omega$$

The current through R_1 is found by KCL at the base node ($I_{R1} = I_{R2} + I_B$):

$$I_{R1} = 100 \mu\text{A} + 10 \mu\text{A} = 110 \mu\text{A}$$

Now, we can find R_1 :

$$R_1 = \frac{V_+ - V_B}{I_{R1}} = \frac{15 \text{ V} - 0 \text{ V}}{110 \mu\text{A}} = \frac{15 \text{ V}}{0.11 \text{ mA}} \approx 136.36 \text{ k}\Omega$$

2 Part 2: PNP in Saturation Mode

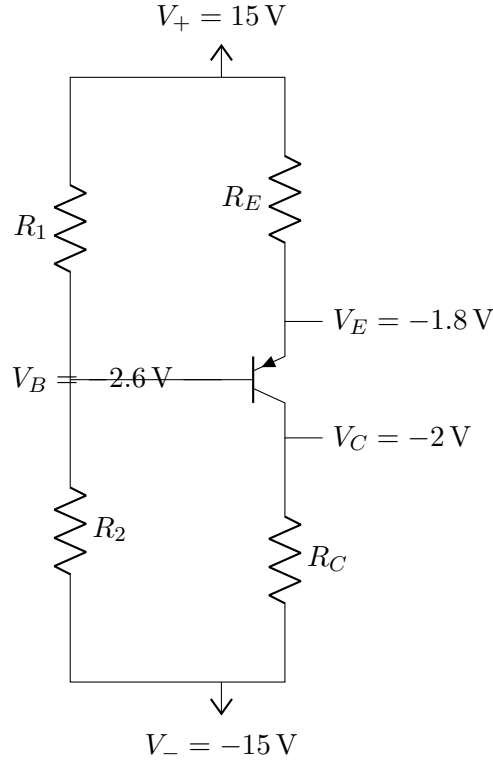


Figure 2: Part 2: PNP in Saturation Mode Circuit (Same topology as Part 1)

2.1 Given Parameters

- **Voltage Supplies:** $V_+ = 15\text{ V}$, $V_- = -15\text{ V}$
- **Design Goals:** $I_C = 1\text{ mA}$, $I_E = 1.2\text{ mA}$, $V_C = -2\text{ V}$, $V_{EC} = 0.2\text{ V}$
- **Assumption:** Saturation model $V_{EB(\text{sat})} = 0.8\text{ V}$

2.2 Calculations

1. Calculate Emitter and Base Voltages (V_E , V_B)

The emitter voltage is found from the given collector voltage and V_{EC} :

$$V_E = V_C + V_{EC} = -2\text{ V} + 0.2\text{ V} = -1.8\text{ V}$$

The base voltage is found using the $V_{EB(\text{sat})}$ assumption:

$$V_B = V_E - V_{EB(\text{sat})} = -1.8\text{ V} - 0.8\text{ V} = -2.6\text{ V}$$

2. Calculate Emitter and Collector Resistors (R_E , R_C)

R_E is calculated using the voltage drop ($V_+ - V_E$) and current I_E :

$$R_E = \frac{V_+ - V_E}{I_E} = \frac{15\text{ V} - (-1.8\text{ V})}{1.2\text{ mA}} = \frac{16.8\text{ V}}{1.2\text{ mA}} = 14\text{ k}\Omega$$

R_C is calculated using the voltage drop ($V_C - V_-$) and current I_C :

$$R_C = \frac{V_C - V_-}{I_C} = \frac{-2\text{ V} - (-15\text{ V})}{1\text{ mA}} = \frac{13\text{ V}}{1\text{ mA}} = 13\text{ k}\Omega$$

3. Calculate β_{forced}

First, find the base current I_B :

$$I_B = I_E - I_C = 1.2\text{ mA} - 1.0\text{ mA} = 0.2\text{ mA}$$

Now, calculate the forced β :

$$\beta_{\text{forced}} = \frac{I_C}{I_B} = \frac{1\text{ mA}}{0.2\text{ mA}} = 5$$

4. Calculate Base Biasing Resistors (R_1 , R_2)

We must again choose a divider current. We will use the $10 \times I_B$ rule for the current through R_2 .

- $I_B = 0.2\text{ mA}$ (flowing out of the base).
- $I_{R2} = 10 \times I_B = 10 \times 0.2\text{ mA} = 2.0\text{ mA}$.

Now, find R_2 :

$$R_2 = \frac{V_B - V_-}{I_{R2}} = \frac{-2.6\text{ V} - (-15\text{ V})}{2.0\text{ mA}} = \frac{12.4\text{ V}}{2.0\text{ mA}} = 6.2\text{ k}\Omega$$

Find I_{R1} using KCL at the base ($I_{R1} = I_{R2} + I_B$):

$$I_{R1} = 2.0\text{ mA} + 0.2\text{ mA} = 2.2\text{ mA}$$

Now, find R_1 :

$$R_1 = \frac{V_+ - V_B}{I_{R1}} = \frac{15\text{ V} - (-2.6\text{ V})}{2.2\text{ mA}} = \frac{17.6\text{ V}}{2.2\text{ mA}} = 8\text{ k}\Omega$$

3 Part 3: Diode-Connected PNP

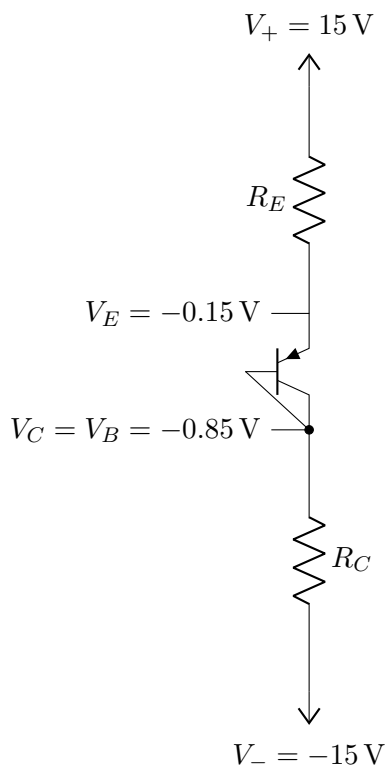


Figure 3: Part 3: Diode-Connected PNP Circuit

3.1 Given Parameters

- **Voltage Supplies:** $V_+ = 15\text{ V}$, $V_- = -15\text{ V}$
- **Design Goals:** $I_C = 1\text{ mA}$
- **Given Component:** $R_E = 15\text{ k}\Omega$
- **Transistor Model:** $\beta = 100$
- **Circuit:** Diode-connected ($V_B = V_C$)
- **Assumption:** Active region $V_{EB(\text{on})} = 0.7\text{ V}$

3.2 Calculations

1. Operating Region

In a diode-connected BJT, the base and collector are shorted, so $V_{BC} = V_B - V_C = 0\text{ V}$. This places the transistor at the boundary between the active and saturation regions. It will operate in the **Active Region**, as it cannot enter saturation (V_{BC} cannot become positive for a PNP).

2. Calculate Currents (I_B , I_E)

$$I_B = \frac{I_C}{\beta} = \frac{1 \text{ mA}}{100} = 0.01 \text{ mA}$$

$$I_E = I_C + I_B = 1 \text{ mA} + 0.01 \text{ mA} = 1.01 \text{ mA}$$

3. Calculate Voltages (V_E , V_C)

The emitter voltage is determined by the V_+ supply, R_E , and I_E :

$$V_E = V_+ - (I_E \cdot R_E) = 15 \text{ V} - (1.01 \text{ mA} \cdot 15 \text{ k}\Omega) = 15 \text{ V} - 15.15 \text{ V} = -0.15 \text{ V}$$

The collector (and base) voltage is found relative to the emitter:

$$V_C = V_B = V_E - V_{EB(\text{on})} = -0.15 \text{ V} - 0.7 \text{ V} = -0.85 \text{ V}$$

4. Calculate Collector Resistor (R_C)

The circuit configuration is $V_+ \rightarrow R_E \rightarrow \text{Emitter}$; $\text{Base} \rightarrow \text{Collector} \rightarrow R_C \rightarrow V_-$. The current flowing out of the shared Base-Collector node and through R_C is the sum of I_B and I_C , which equals I_E .

$$I_{R_C} = I_B + I_C = I_E = 1.01 \text{ mA}$$

R_C is calculated using the voltage drop ($V_C - V_-$) and current I_E :

$$R_C = \frac{V_C - V_-}{I_E} = \frac{-0.85 \text{ V} - (-15 \text{ V})}{1.01 \text{ mA}} = \frac{14.15 \text{ V}}{1.01 \text{ mA}} \approx 14.01 \text{ k}\Omega$$